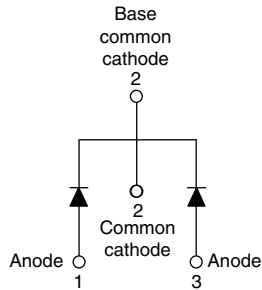


Ultrafast Rectifier, 2 x 8 A FRED Pt®



TO-220AB



FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)



DESCRIPTION/APPLICATIONS

VS-MUR1620CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

PRODUCT SUMMARY	
Package	TO-220AB
$I_{F(AV)}$	2 x 8 A
V_R	200 V
V_F at I_F	0.975 V
t_{rr} typ.	See Recovery table
T_J max.	175 °C
Diode variation	Common cathode

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage	V_{RRM}		200	V
Average rectified forward current	$I_{F(AV)}$	per leg	8.0	A
		total device	16	
Non-repetitive peak surge current per leg	I_{FSM}	Rated V_R , $T_C = 150$ °C	100	
Peak repetitive forward current per leg	I_{FM}	Rated V_R , square wave, 20 kHz, $T_C = 150$ °C	16	
Operating junction and storage temperatures	T_J, T_{Stg}		- 65 to 175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	$I_R = 100$ μ A	200	-	-	V
		$I_F = 8$ A	-	-	0.975	
Forward voltage	V_F	$I_F = 8$ A, $T_J = 150$ °C	-	-	0.895	
		$V_R = V_R$ rated	-	-	5	
Reverse leakage current	I_R	$T_J = 150$ °C, $V_R = V_R$ rated	-	-	250	μ A
			-	-	-	
Junction capacitance	C_T	$V_R = 200$ V	-	25	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8.0	-	nH



VS-MUR1620CTPbF, VS-MUR1620CT-N3

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	$I_F = 1.0\text{ A}$, $di_F/dt = 50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$	-	-	35	ns
		$I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{REC} = 0.25\text{ A}$	-	-	25	
		$T_J = 25\text{ }^\circ\text{C}$	-	20	-	
		$T_J = 125\text{ }^\circ\text{C}$	-	34	-	
Peak recovery current	I_{RRM}	$T_J = 25\text{ }^\circ\text{C}$	-	1.7	-	A
		$T_J = 125\text{ }^\circ\text{C}$	-	4.2	-	
Reverse recovery charge	Q_{rr}	$T_J = 25\text{ }^\circ\text{C}$	-	23	-	nC
		$T_J = 125\text{ }^\circ\text{C}$	-	75	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		- 65	-	175	$^\circ\text{C}$
Thermal resistance, junction to case per leg	R_{thJC}		-	-	3.0	$^\circ\text{C}/\text{W}$
Thermal resistance, junction to ambient per leg	R_{thJA}		-	-	50	
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220AB	MUR1620CT			



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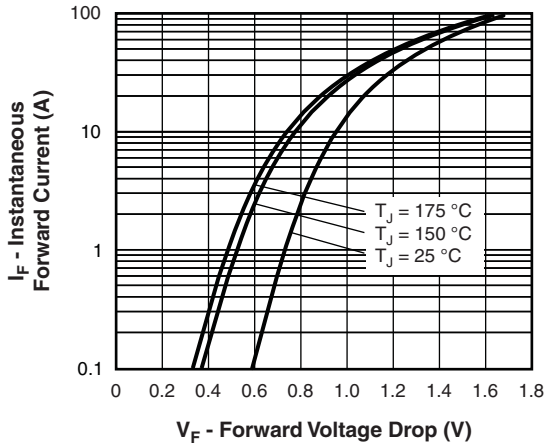


Fig. 1 - Typical Forward Voltage Drop Characteristics

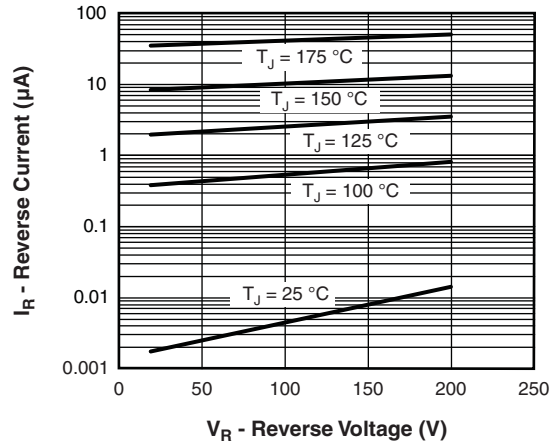


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

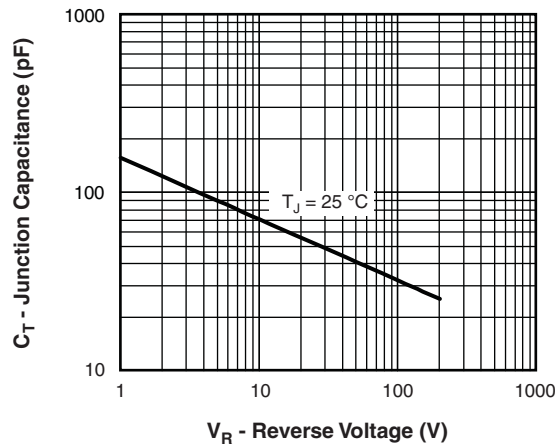


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

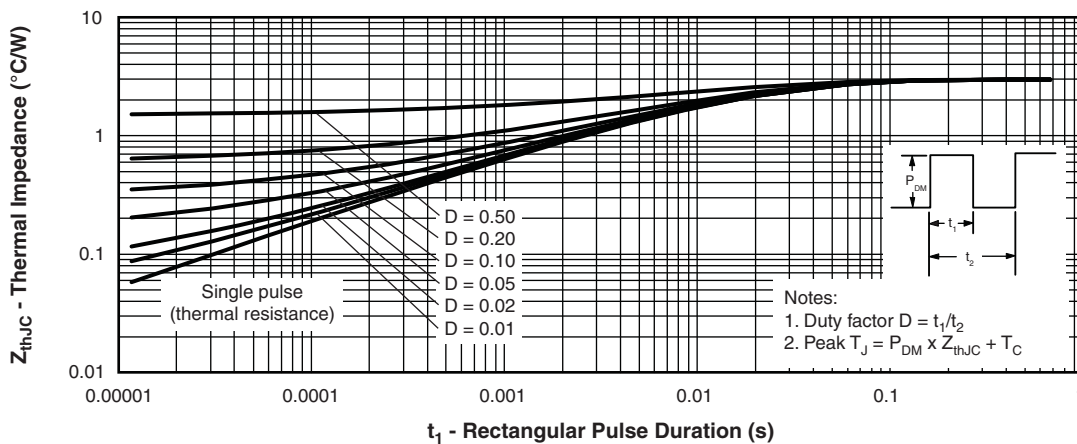


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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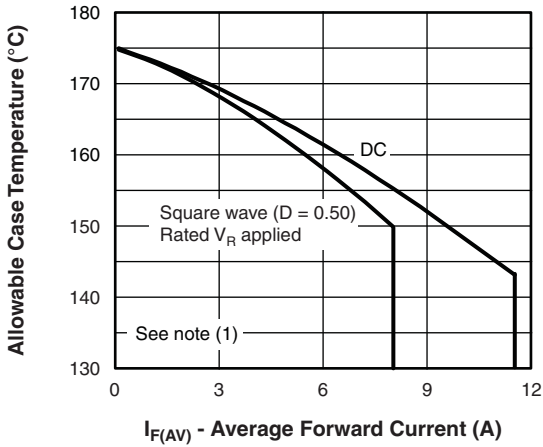


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

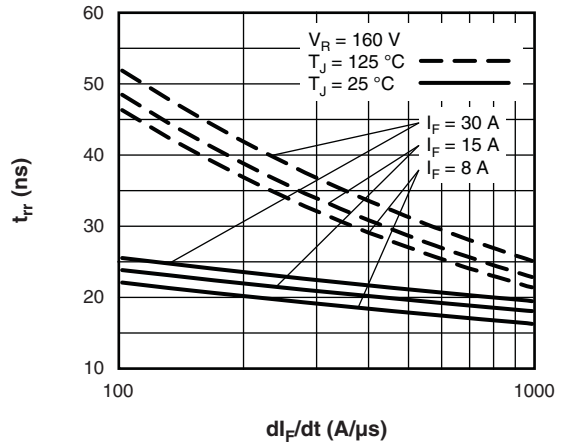


Fig. 7 - Typical Reverse Recovery Time vs. di_F/dt

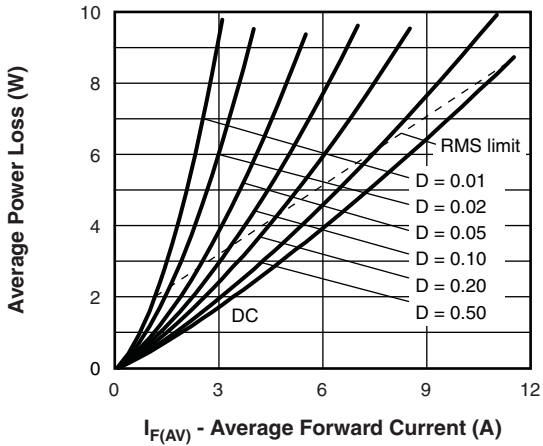


Fig. 6 - Forward Power Loss Characteristics

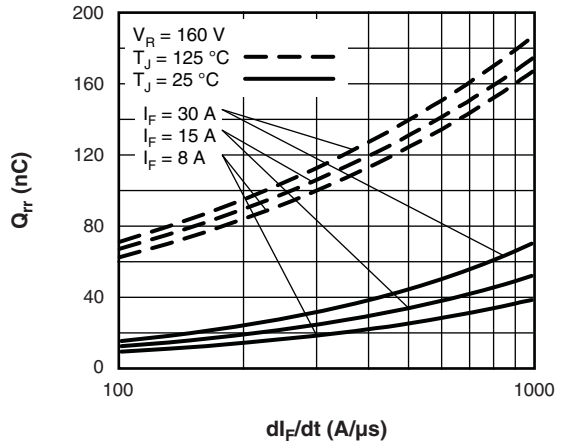


Fig. 8 - Typical Stored Charge vs. di_F/dt

Note

- (1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
- Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
- Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = Rated V_R



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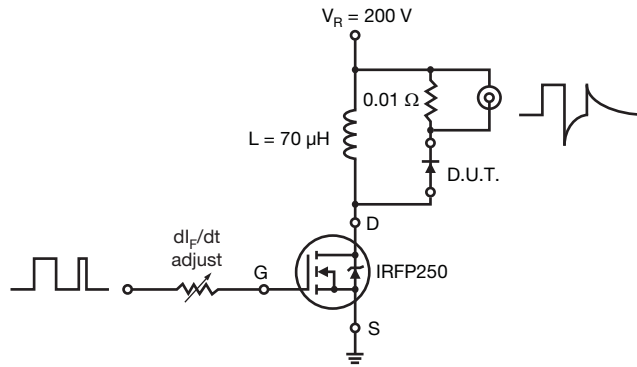
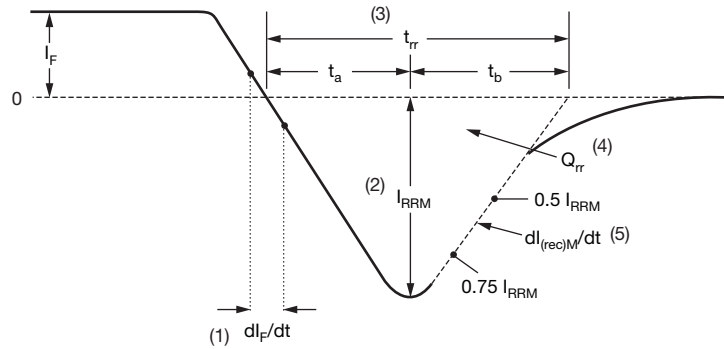


Fig. 9 - Reverse Recovery Parameter Test Circuit



(1) dl_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

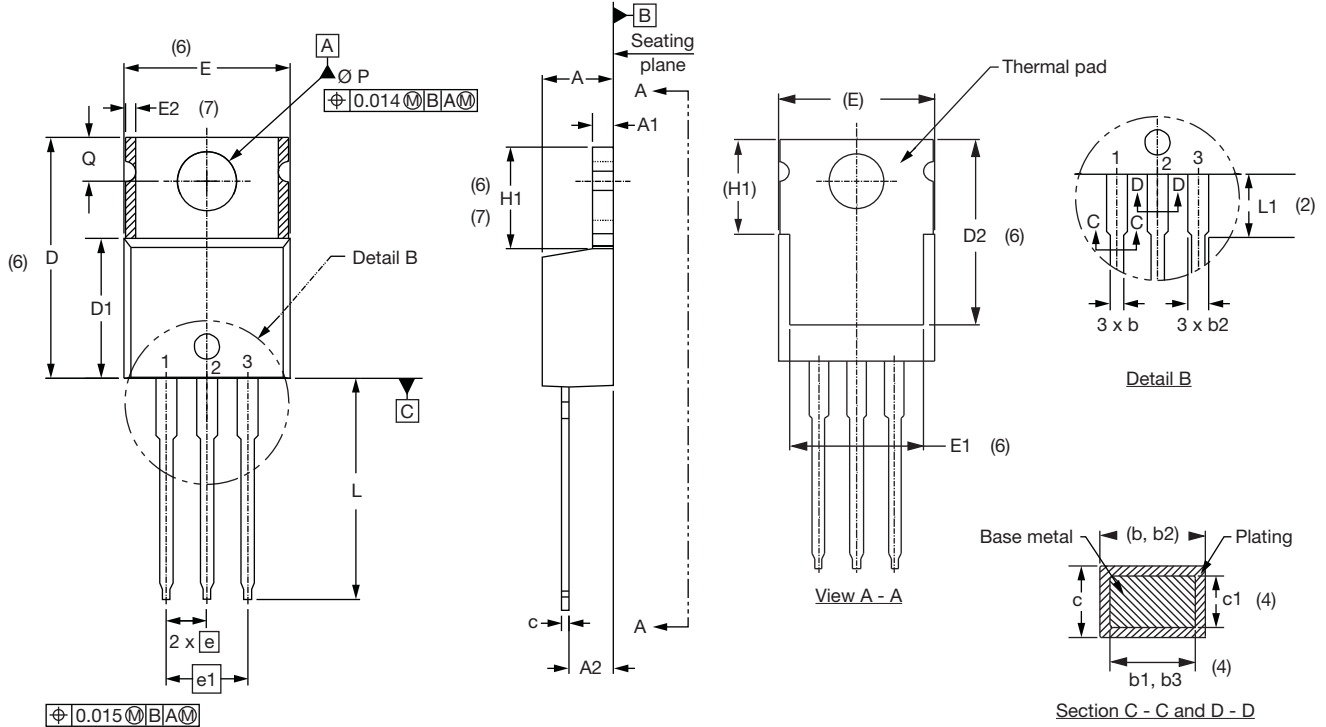


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Outline Dimensions

TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. - Anode/open
- 2. - Cathode
- 3. - Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
c	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
e	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
Ø P	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		